

■ Scope :

- This specification applies to InGaAs PIN photodiode chips.
- Device No. ED-PIN1010VA8

■ Features :

- High response
- Small dark current
- Low back reflection
- Stability
- Good reliability

■ Typical Applications :

- CATV analog receiver
- Optical communication
- Fiber sensor
- Optical parameter test

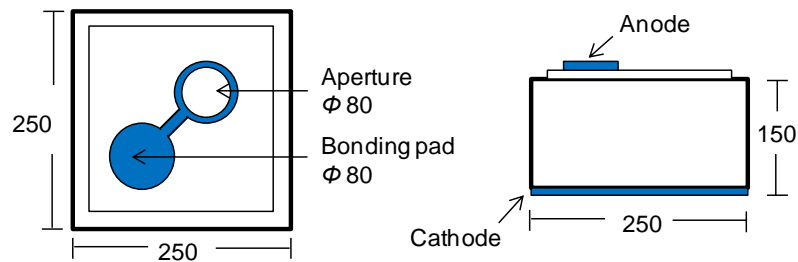
■ Structure :

- Type : PIN diode.
- Electrodes :
Top side (Anode) : Au alloy.
Back side (Cathode) : Au alloy.

■ Size :

- Chip size : 9.8 mils × 9.8 mils (0.25 mm × 0.25 mm).
- Chip thickness : 5.9 ± 1 mils (0.15 ± 0.025 mm).
- Aperture size : $\phi = 3.2$ mils ($\phi = 0.08$ mm).
- Bonding pad (Anode) : $\phi = 3.2$ mils ($\phi = 0.08$ mm).

■ Outline Dimensions: (Unit: μm)



■ Electro-optical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse Dark Current	ID	VR=5V Ee=0mW/cm ²		0.1	1	nA
*Reverse Breakdown Voltage	V(BR)R	IR=1uA Ee=0mW/cm ²	20	40		V
*Forward Voltage	VF	IF=3mA Ee=0mW/cm ²		0.65	0.8	V
Capacitance	Cp	VR=5V f=1MHz		0.45		pF
Responsivity	Resp	VR=5V Wavelength=1310nm	0.8	0.9		A/W
Bandwidth	BW	-		1.25		GHz

*Based on 100% probing